

MS ISSUE FEE PATENT 1781-0247P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant:

Soo Jin CHUA et al.

Conf.:

5461

Appl. No.:

10/633,652

Group:

2812

Filed:

August 5, 2003

Examiner: MULPURI, S.

For:

FORMING INDIUM NITRIDE (INN) AND INDIUM

GALLIUM NITRIDE (INGAN) QUANTUM DOTS

GROWN BY METAL-ORGANIC-VAPOR-

PHASE=EPITAXY (MOCVD)

LARGE ENTITY TRANSMITTAL FORM

HANDCARRY TO:

September 29, 2004

U.S. Patent and Trademark Office 2011 South Clark Place

Customer Window

Crystal Plaza Two, Lobby, Room 1B03

Arlington, VA 22202

Sir:

Transmitted herewith please find an amendment in the aboveidentified application.

The enclosed document is being transmitted via the Certificate of Mailing provisions of 37 C.F.R. § 1.8.

The enclosed document is being transmitted via facsimile.

The fee has been calculated as shown below:

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INDEPENDENT	4	-	4 .	=	0	\$ 86	\$0.00
FIRST PRESENTATION OF A MULTIPLE DEPENDENT CLAIM						\$290	\$0.00
						TOTAL	\$0.00

Appl. No. 10/633,652

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	A check in the amount o	f \$0.00 is enclosed.		
	Please charge Deposit A \$0.00. This form is sub	Account No. 02-2448 in the amount of mitted in triplicate.		
If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.				
		Respectfully submitted,		
		BIRCH, STEWART, KOLASCH & BIRCH, LLP		
		By Null #36,623		
DRN/n 1781-	nua -0247P	P.O. Box 747 Falls Church, VA 22040-0747 (703) 205-8000		
Attac	chment(s)			

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AMENDMENT UNDER 37 C.F.R. § 1.312

HANDCARRY TO:

September 29, 2004

U.S. Patent and Trademark Office 2011 South Clark Place Customer Window, MS ISSUE FEE Crystal Plaza Two, Lobby, Room 1B03 Arlington, VA 22202

Sir:

Pursuant to the provisions of 37 C.F.R. § 1.312, the following amendments and remarks are respectfully submitted in connection with the above-identified application. It is respectfully requested that the following amendments be entered without withdrawing the application from issue.

This amendment includes Amendments to the Specification; Remarks; Substitute Specification and three (3) Replacement Sheets of Drawings.